OPA6428URO

Ultra Red LED Chip

Ultra Bright

GaAs/AlGaInP

1. Material

Substrate GaAs (N Type)
Epitaxial Layer AlGaInP (P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

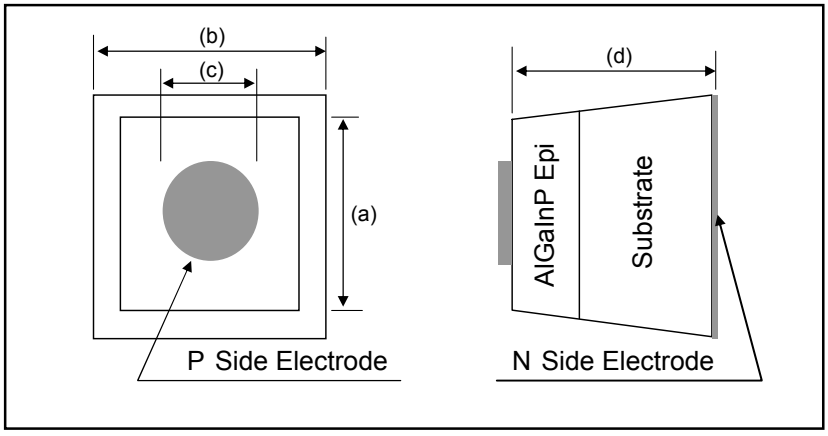
3. Electro-Optical Characteristics

Parameter	Symbol		Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$			1.7		V	IF=1mA
	$V_{F(2)}$			2.2	2.4	V	IF=20mA
Reverse Current	I_R				100	uA	VR=10V
Brightness	I_v	D	30	45		mcd	IF=20mA
		E	40	55			
		F	50	70			
Wavelength	λ_d			631		nm	IF=20mA
	$\Delta\lambda$			20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

4. Mechanical Data

(a) Emission Area ---------- 10mil x 10mil
(b) Bottom Area ---------- 11mil x 11mil
(c) Bonding Pad ---------- 130um
(d) Chip Thickness ---------- 11mil



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